

## AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

### Listing of Claims

Claim 1-22 (canceled)

Claim 23. (Currently amended) A structure for a bit line contact hole, comprising:

- a substrate ;
- a transistor, disposed on the substrate, comprising a gate layer covered by a first insulating layer and comprising a first doped region and a second doped region ~~a doped region~~;
- an inner landing pad, disposed on the first doped region and parts of the transistor, comprising a polysilicon layer;
- a passivation layer serving as a diffusion barrier, formed on the inner landing pad, the transistor, and the substrate, wherein the passivation layer is in contact with the second doped region;
- a second insulating layer comprising doped materials, disposed on the passivation layer, having a flat surface on the passivation layer;
- a contact plug, disposed on the second insulating layer and the passivation, electrically connecting with the inner landing pad; and
- an interconnected landing pad, deposited on the contact plug.

Claim 24. (Original) The structure as claimed in claim 23, wherein thickness of the polysilicon layer of the inner landing pad is about 100~400Å.

Claim 25. (Original) The structure as claimed in claim 23, wherein the material of the passivation layer comprises silicon nitride.

Claim 26. (Original) The structure as claimed in claim 25, wherein thickness of the passivation layer is about 110~130Å.

Claim 27. (Canceled)

Claim 28. (New) A structure for a bit line contact hole, comprising:

- a substrate;
- a transistor, disposed on the substrate, comprising a gate layer covered by a first insulating layer and comprising a first doped region and a second doped region;
- an inner landing pad, disposed on the first doped region and parts of the transistor;
- a passivation layer, disposed on the inner landing pad, the transistor and the substrate, wherein the passivation layer is in contact with the second doped region;
- a second insulating layer, disposed on the passivation layer, having a flat surface on the passivation layer;
- a contact plug, disposed on the second insulating layer and the passivation layer, electrically connecting with the inner landing pad; and
- an interconnected landing pad, deposited on the contact plug.

Claim 29. (New) The structure as claimed in claim 28, wherein thickness of the polysilicon layer of the inner landing pad is about 100~400Å.

Claim 30. (New) The structure as claimed in claim 28, wherein the material of the passivation layer comprises silicon nitride.

Claim 31. (New) The structure as claimed in claim 30, wherein thickness of the passivation layer is about 110~130Å.